

**ABSTRACT**

Defect analysis of an integrated circuit die having a back side opposite circuitry at a circuit side and a liquid crystal layer is enhanced using near infrared (nIR) laser light. According to an example embodiment of the present invention, nIR laser light is  
5 directed to an integrated circuit die having a liquid crystal layer formed over the die. When the die includes a defect that generates heat, the heat generated in the die as a result of the nIR laser light adds to the heat in the die generated as a result of the defect and causes a portion of the liquid crystal layer to change phase near the defect. The phase change is detected and used to identify a portion of the die having a defect.